

AP30N03K

N-Channel Power MOSFET

Description

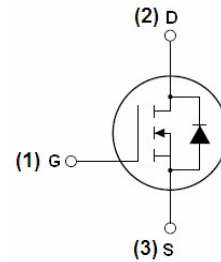
The AP30N03K uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

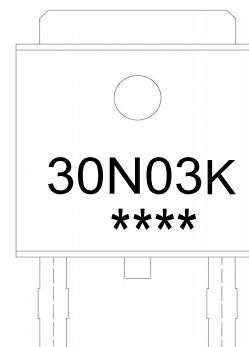
- $V_{DS} = 30V, I_D = 30A$
 $R_{DS(ON)} < 20m\Omega @ V_{GS} = 10V$
 $R_{DS(ON)} < 26m\Omega @ V_{GS} = 5V$
- High density cell design for ultra low R_{dson}
- Fully characterized Avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

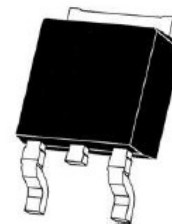
- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible Power Supply



Schematic diagram



Marking and pin assignment



TO-252-2L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
30N03K	AP30N03K	TO-252-2L	-	-	-

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	30	A
Drain Current-Continuous($T_C = 100^\circ C$)	$I_D(100^\circ C)$	22	A
Pulsed Drain Current	I_{DM}	60	A
Maximum Power Dissipation	P_D	45	W
Derating factor		0.4	W/ $^\circ C$
Single pulse avalanche energy ^(Note 5)	E_{AS}	40	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^\circ C$

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Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	2.5	°C/W
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Electrical Characteristics ($T_c=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30	33	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.6	3	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=15A$	-	15	20	m Ω
		$V_{GS}=5V, I_D=20A$	-	20	24	
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=10A$	10	-	-	S
Dynamic Characteristics ^(Note 4)						
Input Capacitance	C_{iss}	$V_{DS}=15V, V_{GS}=0V,$ $F=1.0\text{MHz}$	-	350	-	PF
Output Capacitance	C_{oss}		-	55	-	PF
Reverse Transfer Capacitance	C_{rss}		-	35	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=15V, I_D=1A$ $V_{GS}=10V, R_{GEN}=3.3\Omega$	-	8	-	nS
Turn-on Rise Time	t_r		-	7	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	15	-	nS
Turn-Off Fall Time	t_f		-	5	-	nS
Total Gate Charge	Q_g	$V_{DS}=15V, I_D=8A,$ $V_{GS}=4.5V$	-	4.1	-	nC
Gate-Source Charge	Q_{gs}		-	1.1	-	nC
Gate-Drain Charge	Q_{gd}		-	2.5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{GS}=0V, I_S=1A$	-	0.85	1.2	V
Diode Forward Current ^(Note 2)	I_S		-	-	50	A
Reverse Recovery Time	t_{rr}	$T_J = 25^\circ\text{C}, I_F = 10A$ $di/dt = 100A/\mu s$ ^(Note 3)	-	15	30	nS
Reverse Recovery Charge	Q_{rr}		-	14	28	nC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

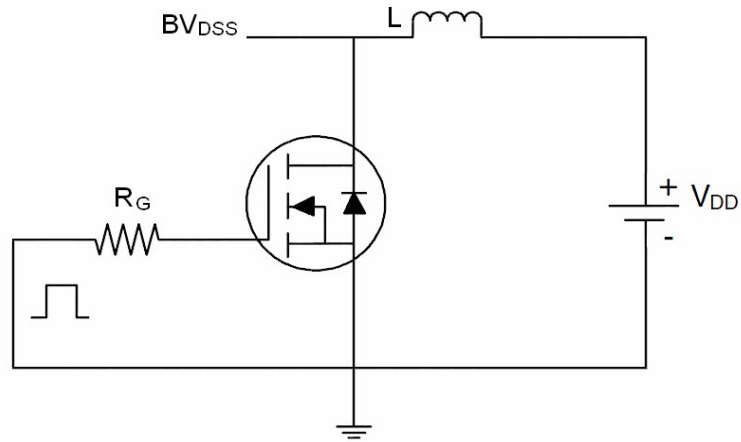
Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition: $T_J=25^\circ\text{C}$, $V_{DD}=15V, V_G=10V, L=0.1\text{mH}, R_g=25\Omega$

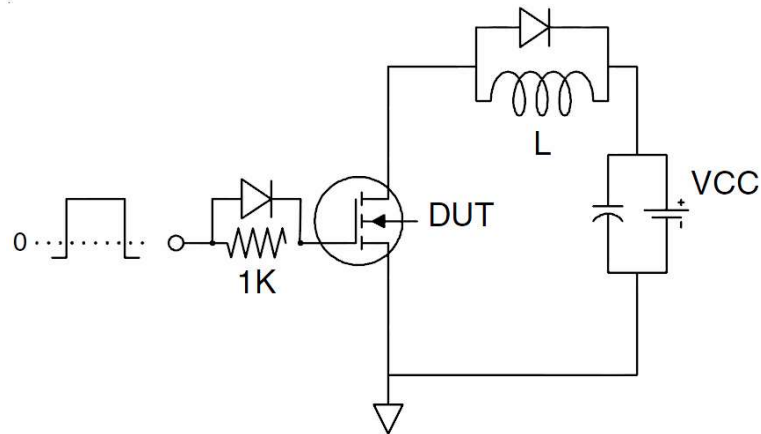
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Test circuit

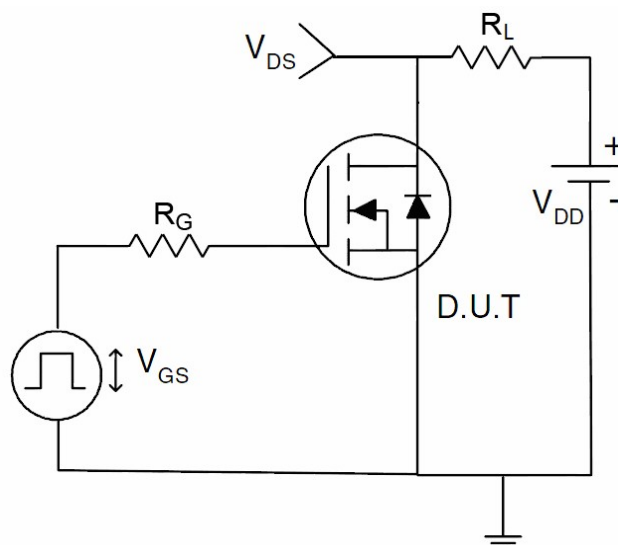
1) E_{AS} test Circuits



2) Gate charge test Circuit:



3) Switch Time Test Circuit:



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Typical Electrical and Thermal Characteristics (Curves)

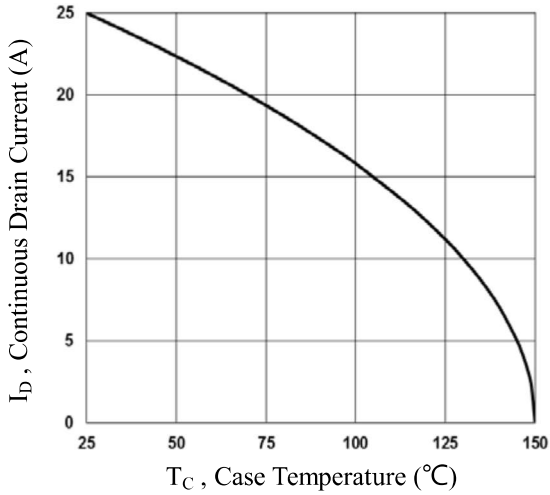


Fig.1 Continuous Drain Current vs. T_c

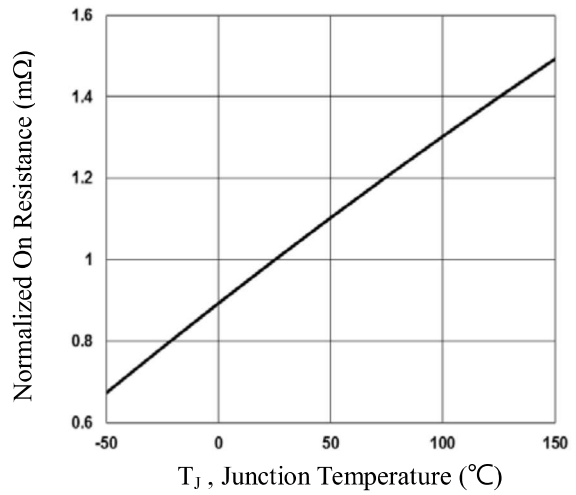


Fig.2 Normalized $R_{DS(on)}$ vs. T_j

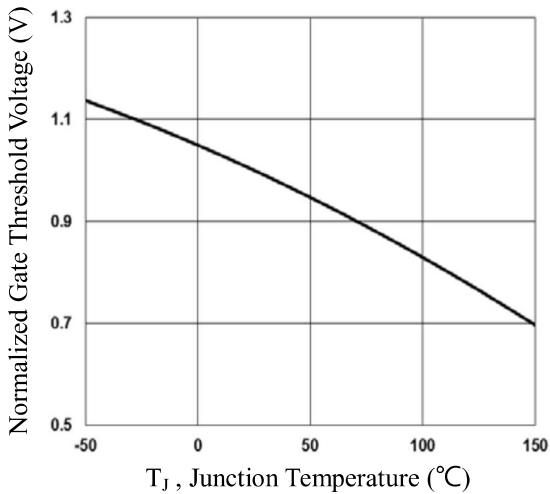


Fig.3 Normalized V_{th} vs. T_j

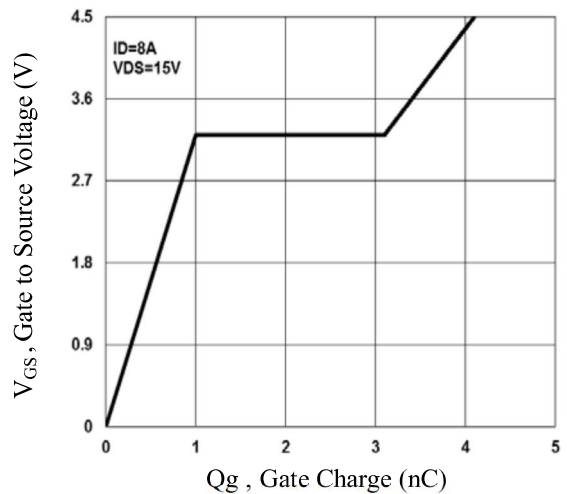


Fig.4 Gate Charge Waveform

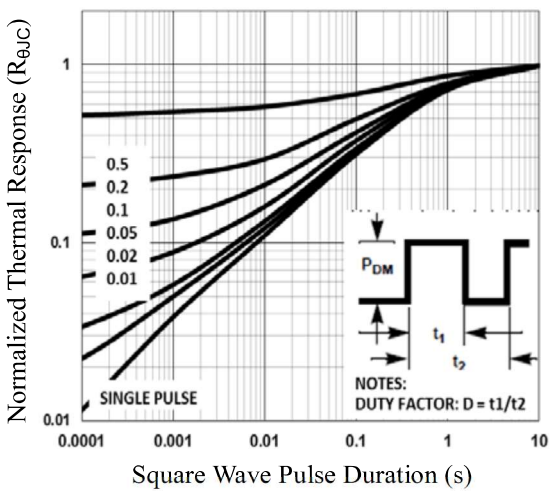


Fig.5 Normalized Transient Response

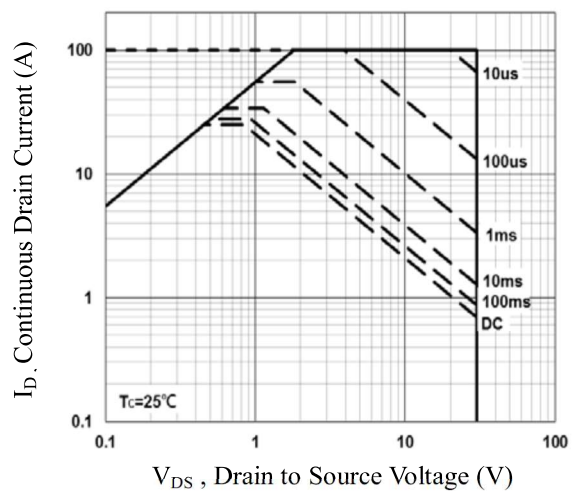


Fig.6 Maximum Safe Operation Area

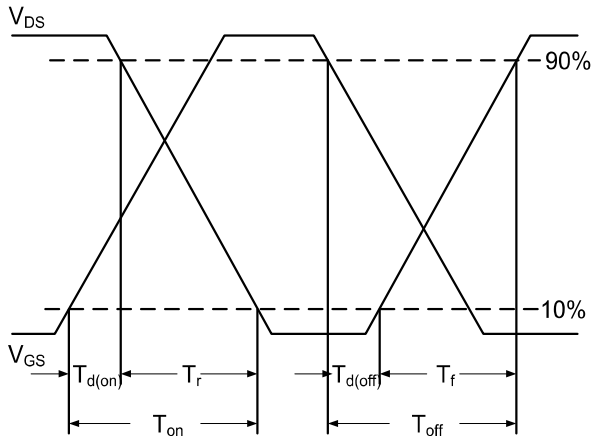


Fig.7 Switching Time Waveform

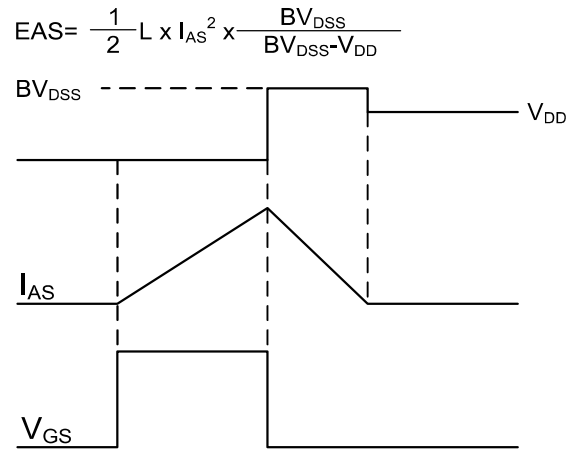
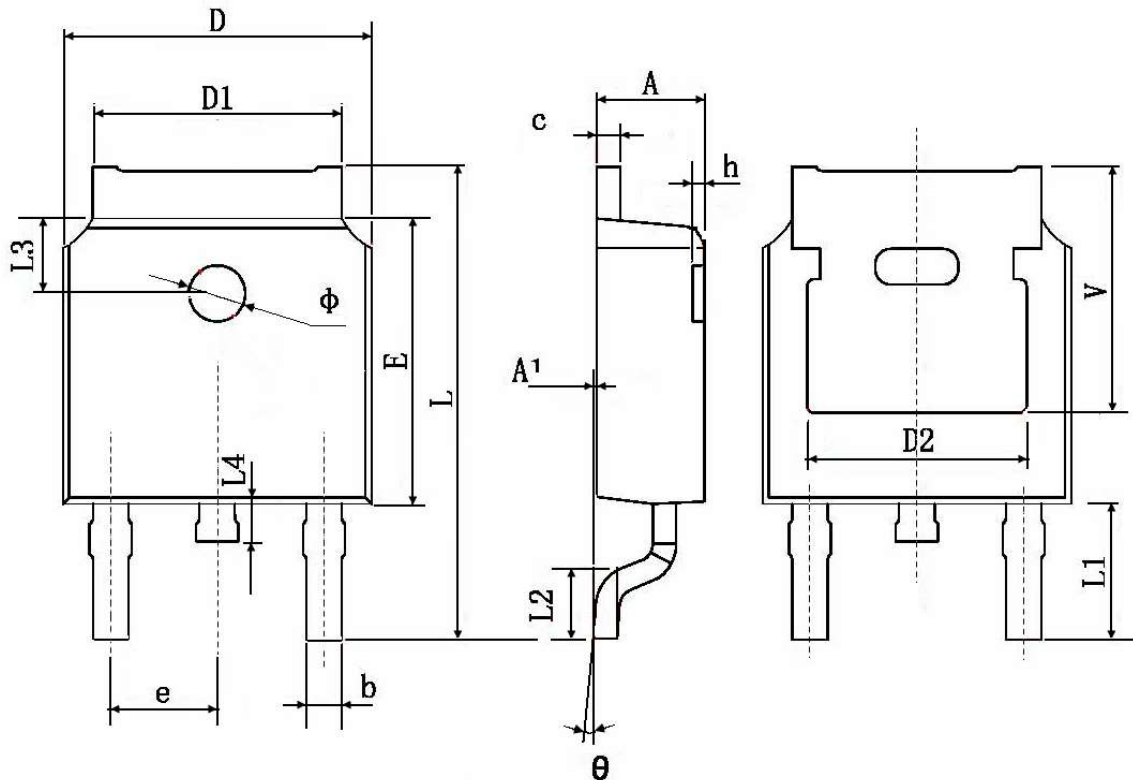


Fig.8 EAS Waveform

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TO-252 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	